

MICRO

ELECTRONICS

NPN
SILICON
TRANSISTOR

DESCRIPTION

BSS38 is PNP silicon planar transistor designed for high voltage video amplifiers in television receivers.

TO-92F



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	VCEO	100V
Collector-Base Voltage	VCBO	120V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	100mA
Continuous Power Dissipation	Pd	300mW
Operating & Storage Junction Temperature	Tj, Tstg	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	LVCEO	100		V	IC=1mA IB=0
Collector-Base Breakdown Voltage	BVCBO	120		V	IC=100μA IE=0
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=100μA IC=0
Collector Cutoff Current	ICBO		200	nA	VCB=90V IE=0
Emitter Cutoff Current	IEBO		100	nA	VEB=4V IC=0
D.C. Current Gain	HFE	20			IC=4mA VCE=1V
Collector-Emitter Saturation Voltage	VCE(sat)		0.7	V	IC=4mA IB=0.4mA
			3		IC=50mA IB=15mA
Base-Emitter Saturation Voltage	VBE(sat)		1.2		IC=4mA IB=0.4mA
Current Gain Bandwidth Product	fT	60		MHz	IC=4mA VCE=10V
Output Capacitance	Cob		4.5	pF	VCB=10V f=1MHz



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